

<p>62000 GaAs LIGHT EMITTING DIODE "PILL PACK" (TYPE GS1140)</p>	<p>Mii OPTOELECTRONIC PRODUCTS DIVISION</p>
------------------------------------------------------------------------------------------------	------------------------------------------------------------

<p>Features:</p> <ul style="list-style-type: none"> • Hermetically sealed • High output, 940nm • Small package • PC board mountable • Spectrally matched to the 61055 series detector 	<p>Applications</p> <ul style="list-style-type: none"> • Incremental encoding • Reflective sensors • Position sensors • Level sensors
-------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------	----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------

DESCRIPTION

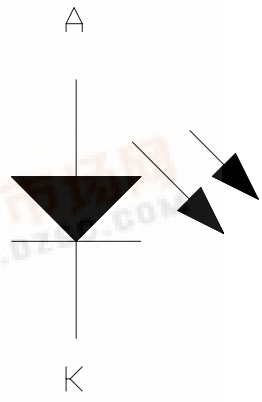
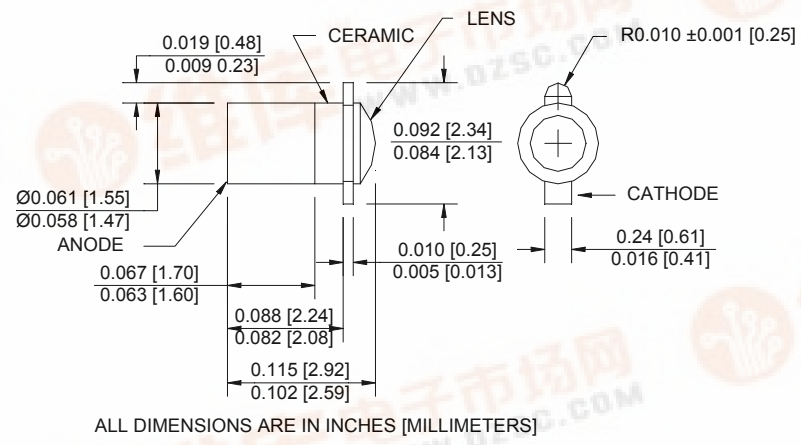
The **62000** is a P-N GaAs Infrared Light Emitting Diode in a lensed "pill" package designed to be mounted in a double-clad printed circuit board. It is spectrally and mechanically matched to companion phototransistors and photodarlington with its narrow beam angle lens and small size which make it ideal for use in optical encoders, card reader arrays, etc. Available binned to customer specifications and/or screened to MIL-PRF-19500.

ABSOLUTE MAXIMUM RATINGS

Storage Temperature.....	-65°C to +150°C
Operating Temperature.....	-65°C to +125°C
Reverse Voltage(at 25°C case temperature).....	2Vdc
Forward Current-Continuous.....	100mA
Soldering Temperature (3 Minutes).....	240°C

Package Dimensions

Schematic Diagram



ELECTRICAL CHARACTERISTICS

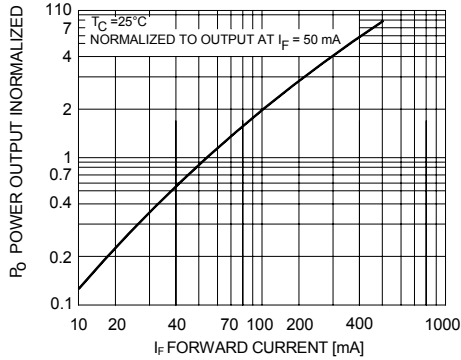
T_A = 25°C unless otherwise specified.

PARAMETER	SYMBOL	MIN	TYP	MAX	UNITS	TEST CONDITIONS	NOTE
Output Power	62000-X01 62000-X02 62000-X03 62000-X04	0.25 0.40 1.0 1.5	0.3 0.65 1.2 1.6		mW	I _F = 50mA	
Forward Voltage	62000-XXX			1.6	V	I _F = 50mA	
Reverse Breakdown Voltage	62000-XXX	2			V	I _B = 10μA	
Radiation Rise Time	62000-XXX		0.7		μs		
Peak Wavelength	62000-XXX		940		nm	I _F = 50mA	
Beam Angle	62000-XXX		20		degrees		1
Forward Max Continuous Current	62000-XXX			100	mA	25°C Case	

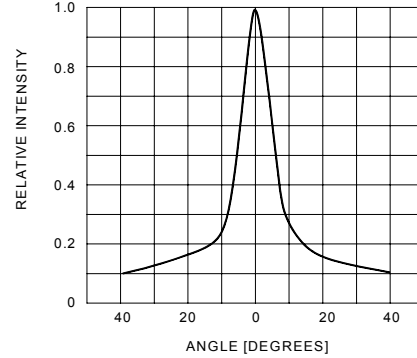
NOTES:

- Low profile 40° lens also available.

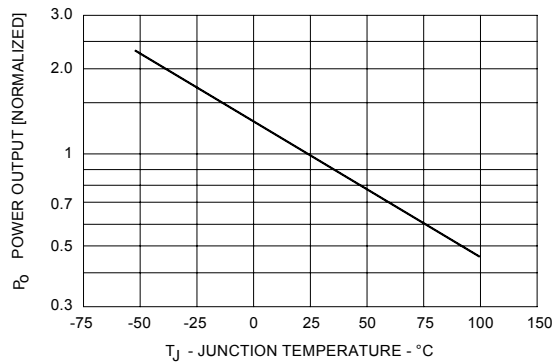
INSTANTANEOUS POWER OUTPUT versus FORWARD CURRENT



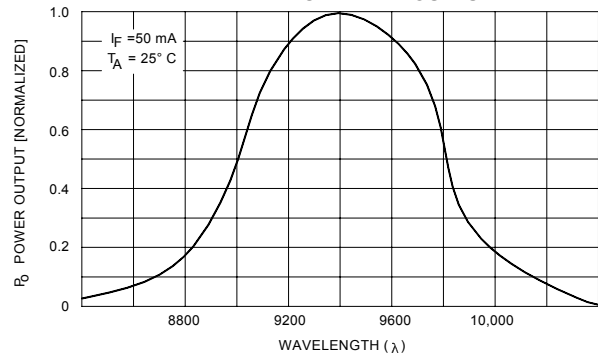
RADIATION PATTERN



POWER OUTPUT versus JUNCTION TEMPERATURE



RELATIVE SPECTRAL OUTPUT



RECOMMENDED OPERATING CONDITIONS:

PARAMETER	SYMBOL	MIN	MAX	UNITS
Forward Current	I_F	50	100	mA

SELECTION GUIDE

PART NUMBER	PART DESCRIPTION	P _o Range
62000-001	GaAs LED in pill package, commercial version	+0.25 mW
62000-101	GaAsLED in pill package (-55° to +100°C) with 100% screening	+0.25 mW
62000-002	GaAs LED in pill package, commercial version	+0.4 mW
62000-102	GaAsLED in pill package (-55° to +100°C) with 100% screening	+0.4 mW
62000-003	GaAs LED in pill package, commercial version	+1 mW
62000-103	GaAsLED in pill package (-55° to +100°C) with 100% screening	+1 mW
62000-004	GaAs LED in pill package, commercial version	+1.5 mW
62000-104	GaAsLED in pill package (-55° to +100°C) with 100% screening	+1.5 mW